Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	-60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = -10V	T_A = +25°C	I_D	-3	A
	T_A = +70°C		-2.4	
Maximum Body Diode Continuous Current		I_S	-2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	-15	A
Single Pulsed Avalanche Current (Note 7)		I_{AS}	-16	A
Single Pulsed Avalanche Energy (Note 7)		E_{AS}	13	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	1.2	W
	T_A = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	104	°C/W
	t<10s		51	
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	2.2	W
	T_A = +70°C		1.4	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	60	°C/W
	t<10s		30	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	7.6	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-60	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -48V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1	—	-3	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	110	150	mΩ	V_{GS} = -10V, I_D = -2.2A
			130	185		V_{GS} = -4.5V, I_D = -1.8A
Diode Forward Voltage	V_{SD}	—	-0.75	-0.95	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	708	—	pF	V_{DS} = -30V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	39	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	32	—	pF	
Gate Resistance	R_g	—	17	28	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	6.2	—	nC	V_{DS} = -30V, I_D = -12A
Total Gate Charge (V_{GS} = -10V)	Q_g	—	14	—	nC	
Gate-Source Charge	Q_{gs}	—	2.8	—	nC	
Gate-Drain Charge	Q_{gd}	—	3.1	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.2	—	ns	V_{DS} = -30V, R_L = 2.5Ω, V_{GS} = -10V, R_G = 3Ω
Turn-On Rise Time	t_R	—	23	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	33	—	ns	
Turn-Off Fall Time	t_F	—	39	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	22	—	ns	I_F = -12A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	17	—	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. UIS in production with L = 0.1mH, starting T_A = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

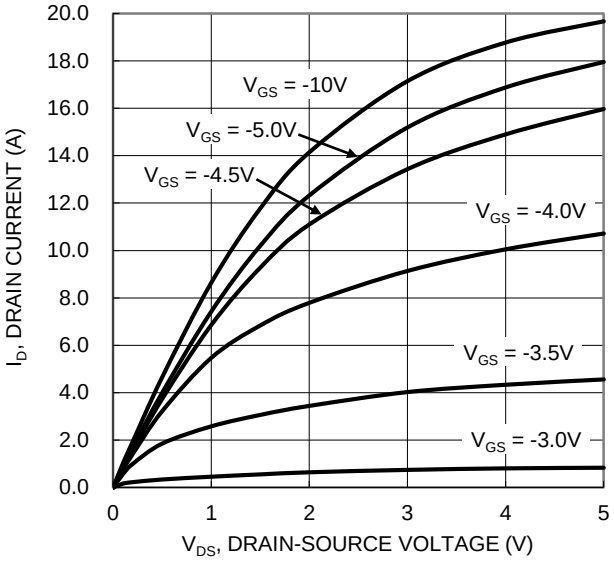


Figure 1. Typical Output Characteristic

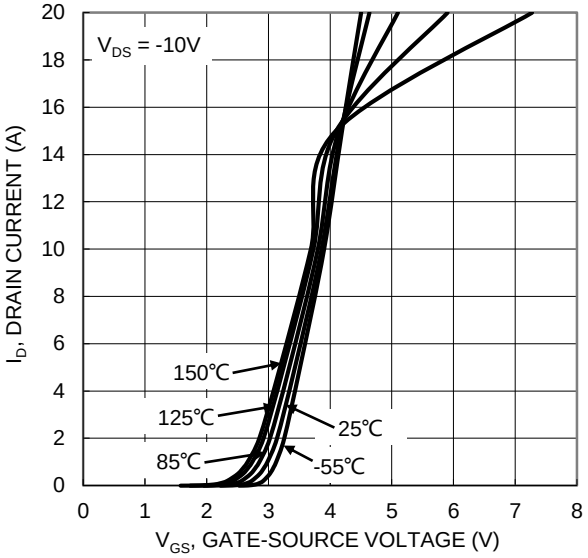


Figure 2. Typical Transfer Characteristic

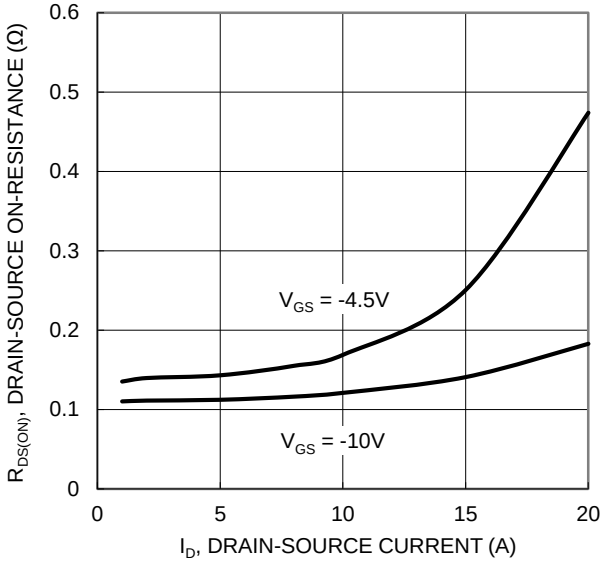


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

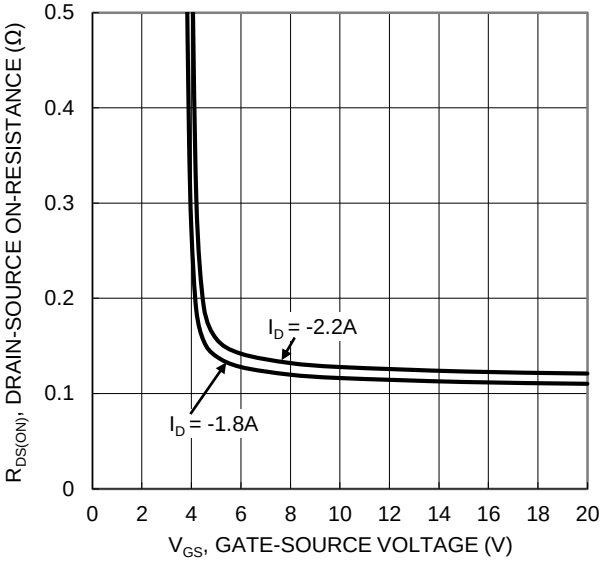


Figure 4. Typical Transfer Characteristic

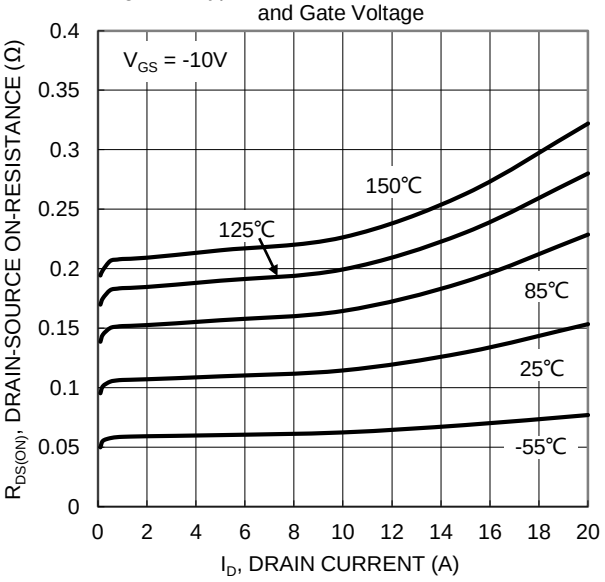


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

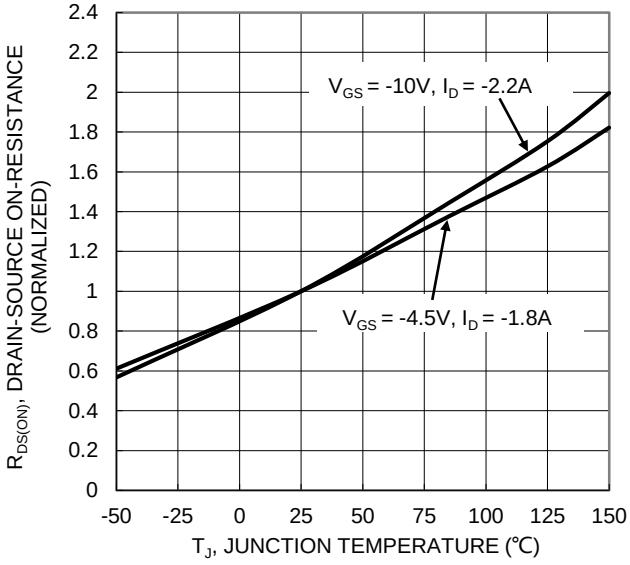


Figure 6. On-Resistance Variation with Temperature

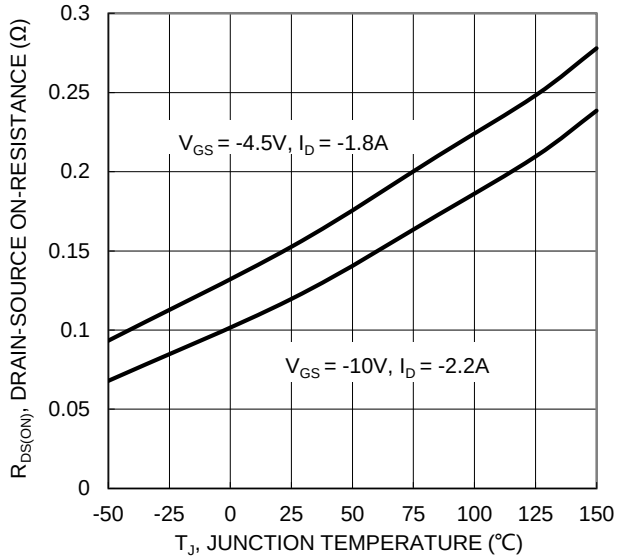


Figure 7. On-Resistance Variation with Temperature

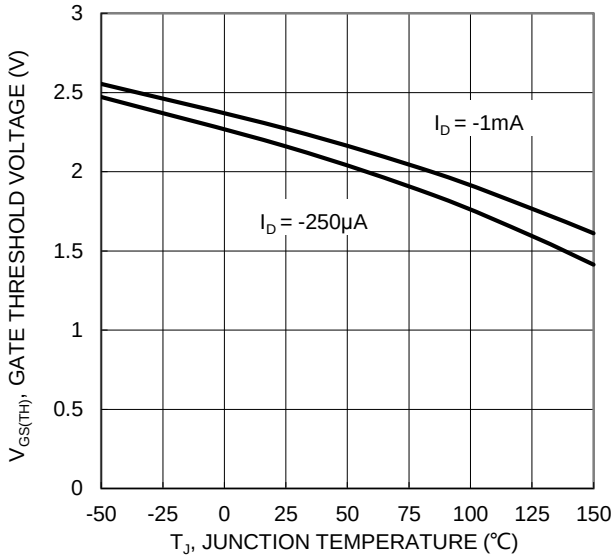


Figure 8. Gate Threshold Variation vs. Junction Temperature

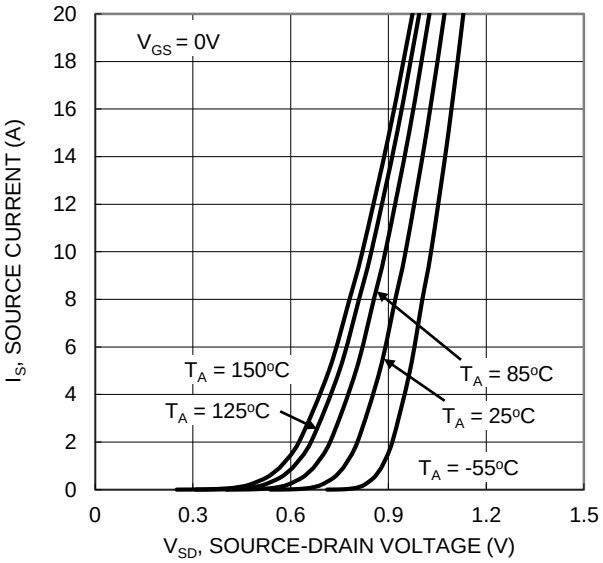


Figure 9. Diode Forward Voltage vs. Current

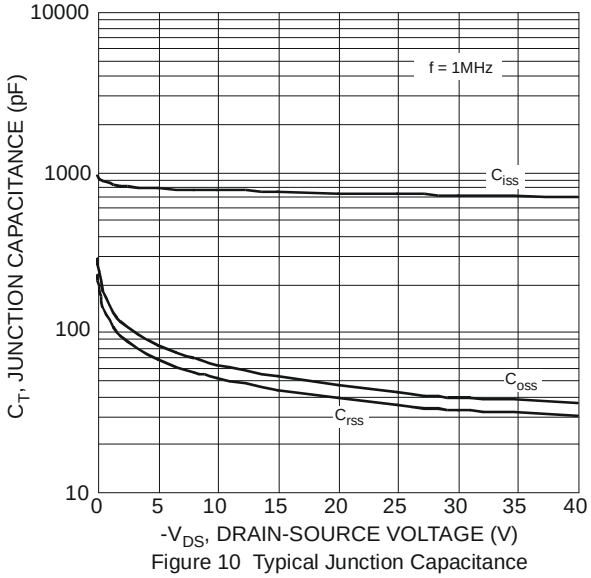


Figure 10 Typical Junction Capacitance

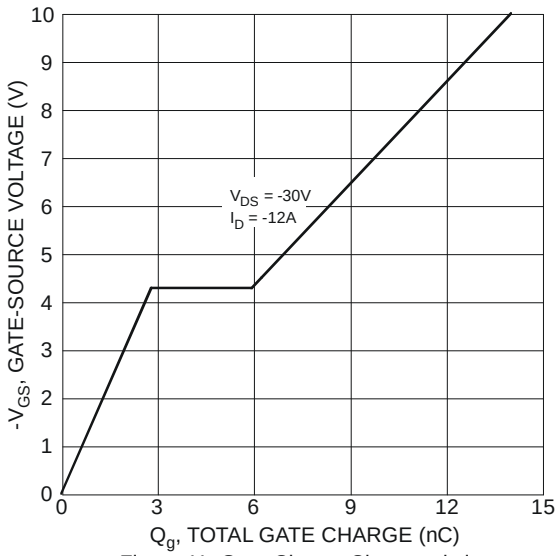


Figure 11 Gate-Charge Characteristics

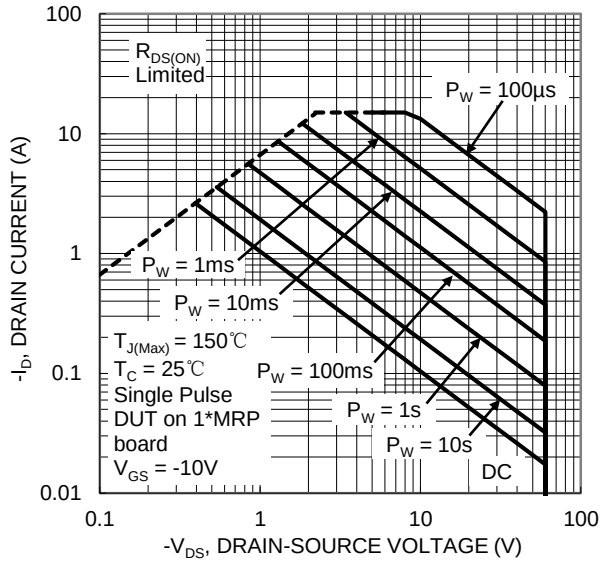


Figure 12. SOA, Safe Operation Area

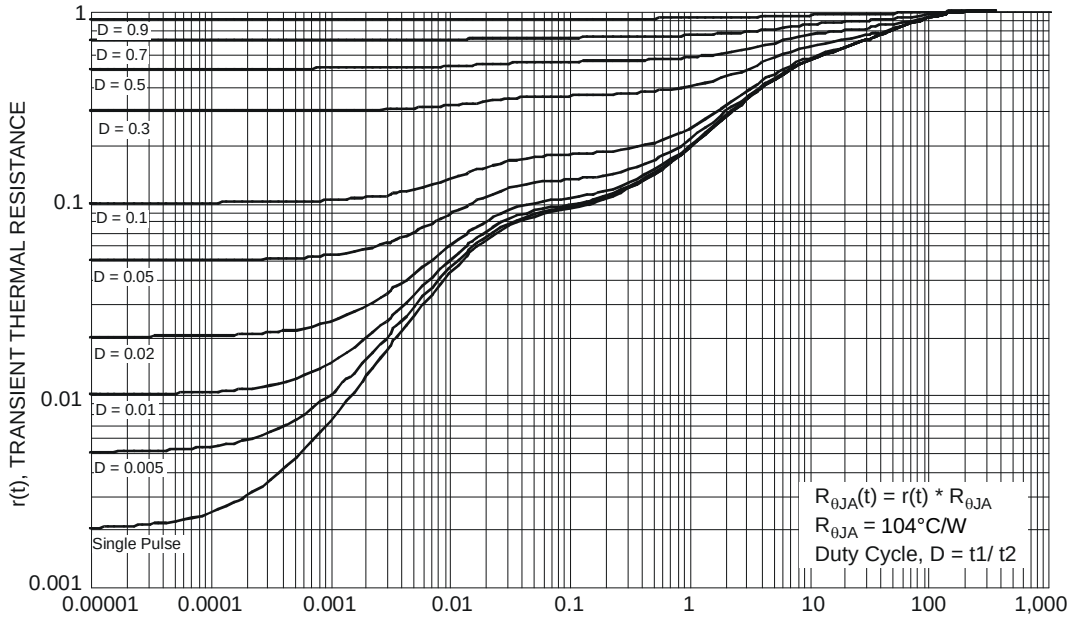
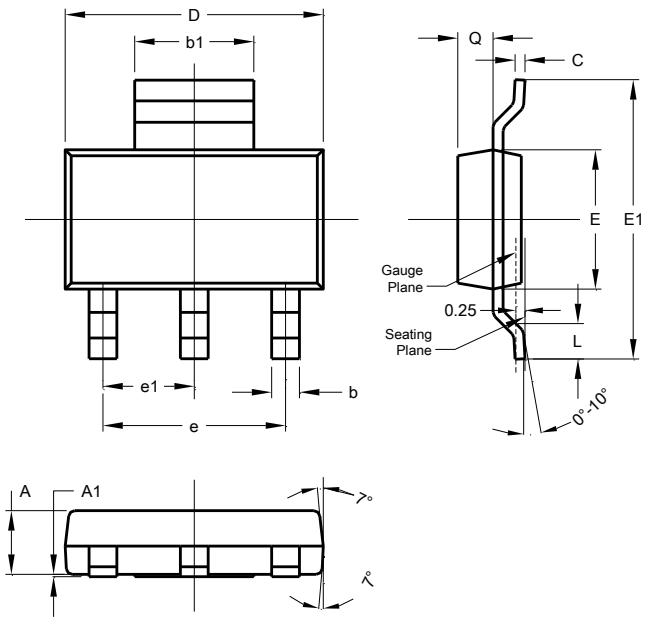


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223

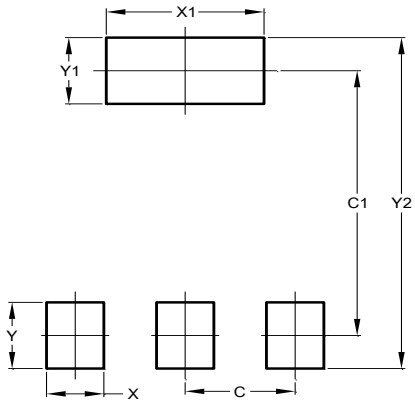


SOT223			
Dim	**Min**	**Max**	**Typ**
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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